Central Semiconductor Corp.
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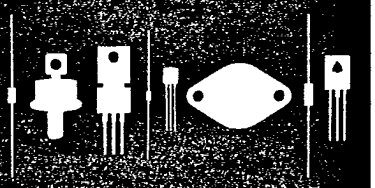
Central™ Semiconductor Corp.
145 Adams Avenue
Hauppauge, New York 11788



PN4888
PN4889

PNP SILICON TRANSISTOR

JEDEC TO-92 CASE (EBC)

DESCRIPTION

The CENTRAL SEMICONDUCTOR PN4888 series types are molded epoxy silicon PNP transistors designed for high voltage amplifier applications.

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	SYMBOL		UNIT
Collector - Base Voltage	V_{CBO}	150	V
Collector - Emitter Voltage	V_{CEO}	150	V
Emitter - Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	100	mA
Power Dissipation	P_D	625	mW
Power Dissipation (T_C=25°C)	P_D	1.0	W
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +150	°C
Thermal Resistance	ΘJA	200	°C/W
Thermal Resistance	ΘJC	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	PN4888 MIN	PN4888 MAX	PN4889 MIN	PN4889 MAX	UNIT
I_{CBO}	V_{CB}=100V		50		10	nA
I_{CBO}	V_{CB}=100V, T_A=65°C		2.5		0.5	µA
I_{EBO}	V_{EB}=4.0V		50		10	nA
BV_{CBO}	I_C=100µA	150		150		V
BV_{CES}	I_C=100µA	150		150		V
BV_{CEO}	I_C=2.0mA	150		150		V
BV_{EBO}	I_E=10µA	6.0		6.0		V
$V_{CE(SAT)}$	I_C=10mA, I_B=1.0mA		0.5		0.5	V
$V_{BE(SAT)}$	I_C=10mA, I_B=1.0mA		0.9		0.9	V
$V_{BE(ON)}$	V_{CE}=10V, I_C=1.0mA		0.8		0.7	V
h_{FE}	V_{CE}=10V, I_C=100µA	-		60		
h_{FE}	V_{CE}=10V, I_C=1.0mA	30		70		
h_{FE}	V_{CE}=10V, I_C=10mA	40	400	80	300	
h_{fe}	V_{CE}=10V, I_C=1.0mA, f=20 MHz	30	160	40	160	MHz
f_T	V_{CE}=10V, I_C=1.0mA, f=1.0kHz	30	500	65	400	kHz
h_{oe}	V_{CE}=10V, I_C=1.0mA, f=1.0kHz	1.4	40	3.0	25	µmhos
h_{re}	V_{CE}=10V, I_C=1.0mA, f=1.0kHz		-		5.0	$x10^{-4}$
h_{ie}	V_{CE}=10V, I_C=1.0mA, f=1.0kHz	0.75	20	1.7	12	kΩ
C_{ob}	V_{CB}=20V, I_E=0, f=1.0MHz		4.0		4.0	pF
C_{ib}	V_{EB}=0.5V, I_C=0, f=1.0MHz		30		25	pF
NF	V_{CE}=5.0V, I_C=250µA, Rs=1.0kΩ, BW=15.7kHz, f=10Hz to 10kHz		-		4.0	dB
NF	V_{CE}=5.0V, I_C=30µA, Rs=10kΩ, BW=150Hz, f=1.0kHz		-		3.0	dB
NF	V_{CE}=5.0V, I_C=250µA, Rs=1.0kΩ, BW=1.5kHz, f=10kHz		-		3.0	dB
NF	V_{CE}=5.0V, I_C=250µA, Rs=1.0kΩ, BW=15Hz, f=100Hz		-		10	dB
NF	V_{CE}=10V, I_C=1.0mA, Rs=1.0kΩ, BW=2.0Hz, f=1.0MHz		-		4.0	dB